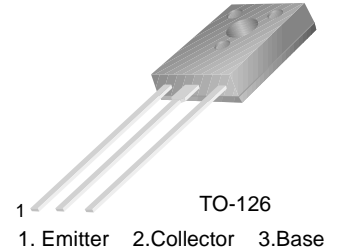


■■ APPLICATION: Low Frequency Power Amplifier Applications.

■■ MAXIMUM RATINGS (Ta=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V _{CBO}	120	V
Collector-emitter voltage	V _{CEO}	120	V
Emitter-base voltage	V _{EBO}	5	V
Collector current	I _C	1	A
Power Dissipation(Ta=25°C)	P _C	1	W
Power Dissipation(Tc=25°C)	P _C	8	W
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{stg}	-55~150	°C



■■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
Common Emitter DC Current Gain	h _{FE1}	60		320		V _{CE} = 5V, I _C = 50mA
	h _{FE2}	20				V _{CE} = 5V, I _C = 500mA
Collector Cut-off Current	I _{CBO}			1	μ A	V _{CB} = 50V, I _E =0
Emitter Cut-off Current	I _{EBO}			1	μ A	V _{EB} = 4V, I _C =0
Collector-Base Breakdown Voltage	BV _{CBO}	120			V	I _C = 0.01mA, I _E =0
Collector-Emitter Breakdown Voltage	BV _{CEO}	120			V	I _C = 1mA, I _B =0
Emitter-Base Breakdown Voltage	BV _{EBO}	5			V	I _E = 0.01mA, I _C =0
Collector-Emitter Saturation Voltage	V _{CE(sat)}		0.15	0.4	V	I _C = 500mA, I _B = 50mA
Base-Emitter Saturation Voltage	V _{BE(sat)}		0.85	1.2	V	I _C = 500mA, I _B = 50mA
Gain bandwidth product	f _T	50	130		MHz	I _C = 50mA, V _{CE} = 10V
Output Capacitance	C _{ob}		20		pF	V _{CB} = 10V, I _E =0, f = 1MHz
Fall Time	t _f		100		ns	V _{CE} = 12V, P _w =20 μ s I _C =10I _{B1} =-10I _{B2} = 500 mA
Turn-off Time	t _{off}		500		ns	
Storage Time	t _{stg}		700		ns	

■■ hFE Classification

Classification	D	E	F
h _{FE1}	60~120	100~200	160~320